



TO-92MOD Plastic-Encapsulated Transistors

2SA966 TRANSISTOR (PNP)

FEATURE

Power dissipation

$$P_{CM}: 0.9 \text{ W} (T_{amb}=25^{\circ}\text{C})$$

Collector current

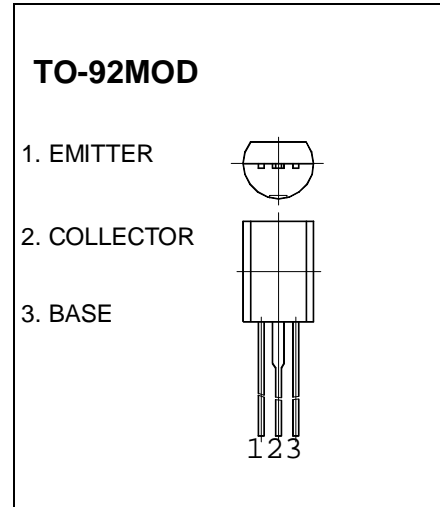
$$I_{CM}: -1.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -30 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C} \text{ to } +150^{\circ}\text{C}$$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test conditions | MIN | MAX | UNIT |
|--------------------------------------|---------------|--|-----|------|---------------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C = -1\text{mA}, I_E = 0$ | -30 | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C = -10\text{mA}, I_B = 0$ | -30 | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E = -1\text{mA}, I_C = 0$ | -5 | | V |
| Collector cut-off current | I_{CBO} | $V_{CB} = -30\text{V}, I_E = 0$ | | -0.1 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = -5\text{V}, I_C = 0$ | | -0.1 | μA |
| DC current gain | $h_{FE(1)}$ | $V_{CE} = -2\text{V}, I_C = -500\text{mA}$ | 100 | 320 | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -1.5\text{A}, I_B = -0.03\text{A}$ | | -2 | V |
| Base-emitter voltage | V_{BE} | $I_C = -500\text{mA}, V_{CE} = -2\text{V}$ | | -1 | V |
| Transition frequency | f_T | $V_{CE} = -2\text{V}, I_C = -500\text{mA}$ | 100 | | MHz |

CLASSIFICATION OF $h_{FE(1)}$

| Rank | O | Y |
|-------|---------|---------|
| Range | 100-200 | 160-320 |